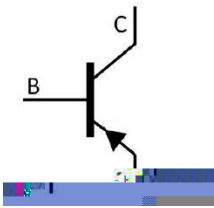


Rev. C Oct.-2018

TO-220 PNP Silicon PNP transistor in a TO-220 Plastic Package.

BR2N 6488
Complement to BR2N 6488.

Use in general-purpose amplifier and switching applications.



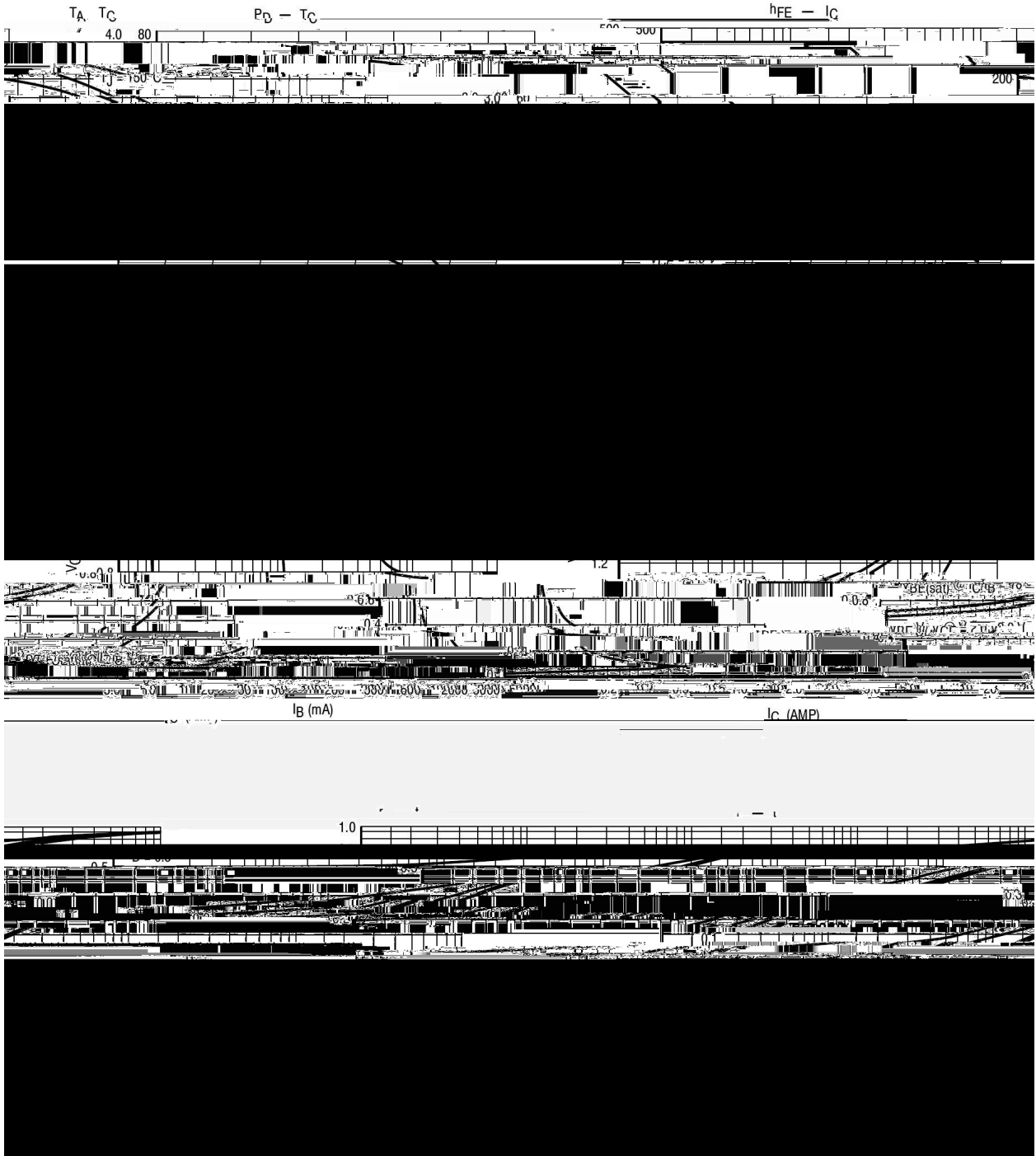
PIN1 Base PIN 2 Collector PIN 3 Emitter

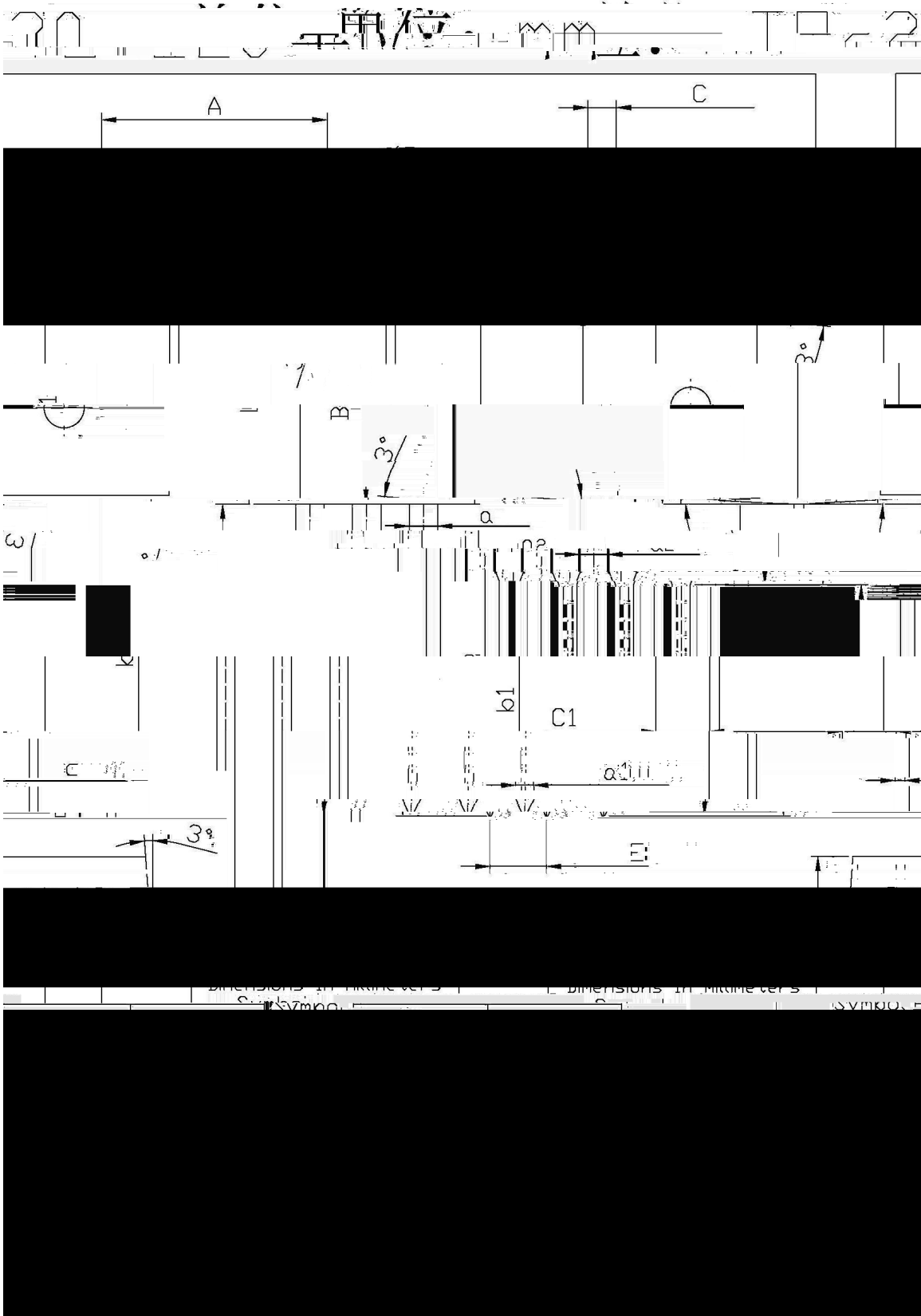
See Marking Instructions.

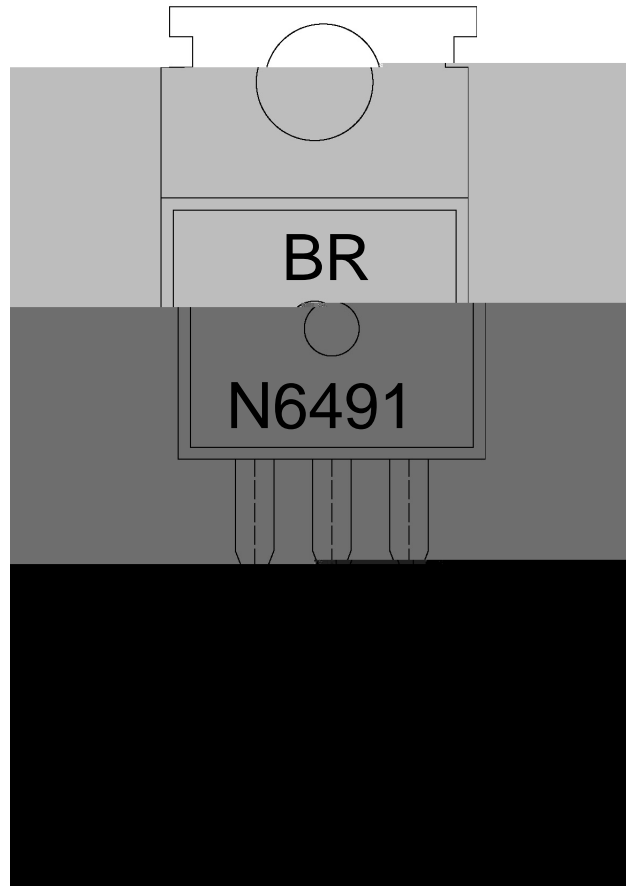
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-90	V
Collector to Emitter Voltage	V_{CEO}	-80	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-15	A
Base Current	I_B	-5.0	A
Total Power Dissipation	$P_D(T_C=25^\circ\text{C})$	75	W
	$P_D(T_A=25^\circ\text{C})$	1.8	W
Operating and Storage Junction Temperature Range	$T_j T_{stg}$	-65 +150	
Thermal Resistance Junction to Case	R_{JC}	1.67	/W
Thermal Resistance Junction to Ambient	R_{JA}	70	/W

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Emitter Sustaining Voltage	$V_{CEO(sus)}$	$I_C=-200\text{mA}$ $I_B=0$	-80			V
Collector Emitter Sustaining Voltage	V_{CEX}	$I_C=-200\text{mA}$ $V_{BE}=-1.5\text{V}$	-90			V
Collector Cut-Off Current	I_{CEX}	$V_{CB}=-85\text{V}$ $V_{BE(off)}=-1.5\text{V}$			-500	μA
		$V_{CB}=-80\text{V}$ $V_{BE(off)}=-1.5\text{V}$ $T_C=150$			-5.0	μA
Collector Cut-Off Current	I_{CEO}	$V_{CE}=-40\text{V}$ $I_B=0$			-1.0	mA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-5.0\text{V}$ $I_C=0$			-1.0	mA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=-4.0\text{V}$ $I_C=-5.0\text{A}$	20		150	
	$h_{FE(2)}$	$V_{CE}=-4.0\text{V}$ $I_C=-15\text{A}$	5.0			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-5.0\text{A}$ $I_B=-0.5\text{A}$			-1.3	V
		$I_C=-15\text{A}$ $I_B=-5.0\text{A}$			-3.5	V

Base to Emitter On Voltage V







BR

N6491

Note:

BR: Company Code

N6491: Product Type.

****: Lot No. Code, code change with Lot No.

